# **SIMULTANEOUS THERMOANALYTICAL EXAMINATIONS** OF  $Si-X$ ,  $S$ ,  $O<sub>s</sub>$  ( $X = Na$ ,  $K$ ) BINARY SYSTEMS

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### ABSTRACT

The non-isothermal thermoanalytical curves  $(T, TG, DTG)$  and DTA) of various molar ratios of binary mixtures of  $Si-X$ ,  $S_2O_8$  have been examined using a MOM derivatograph. Silicon can catalytically lower the T<sub>i</sub> values of both persulfates by about  $15-20\degree C$ , and that of the corresponding pyrosulfates by 10°C. No solid-state reaction has been observed between Si and the two peroxosalts or their pyrosulfates but their by-products,  $X$ ,  $SO<sub>a</sub>$  $(X = Na, K)$ , reacted and yielded the respective mixed oxides,  $Na<sub>2</sub>Si<sub>3</sub>O<sub>7</sub>$  and  $K<sub>2</sub>Si<sub>2</sub>O<sub>5</sub>$ , and gaseous  $SO_3$  and  $SO_2$ . Intermediate and final products are identified by X-ray diffraction. Silicon powder is not oxidised in static air even at temperatures as high as 1050°C.

#### **INTRODUCTION**

For the last three decades Si has been used in the presence of some dopants as a p- or n-type semiconductor. It is the most commonly used semiconductor and today constitutes about 90% of the electronic industry for manufacturing transistors and integrated circuits. Another important use is in the building of Si-based solar energy cells for terrestrial applications such as direct conversion of solar energy into electricity. As insulators and semiconductors for axial and other cables, Si rubbers are in huge industrial demand. Silicone greases and oils are used for vacuum lines, baths and as lubricating oils since they have good antioxidation stability [l]. The TG, DTG and DTA analyses were performed on semiconductor chalcogenides [2]. The chemical literature lacks data on the derivatographic thermoanalytical behaviour of pure Si, alone or in mixtures with peroxosalts, and their solid thermal decomposition products. In the present paper we aim to determine the thermal stability, catalytic activity and types of compounds formed during non-isothermal solid-state reactions between Si and other reactants\_

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#### EXPERIMENTAL

All of the molar ratio binary mixtures were prepared from analytical grade reagents. Si (0.05  $\mu$ m mesh) was puriss grade from Fluka AG, Buchs;  $\alpha$ -alumina, excited at 1300°C, was inert reference material, Na<sub>2</sub>S<sub>2</sub>O<sub>8</sub> and  $K_2S_2O_8$  were from BDH.

Apparatus, measurement techniques, procedure and X-ray diffraction analyses were as described previously [3].

#### RESULTS AND DISCUSSION

## *Thermoanalysis of Si*

No signs of physical or chemical changes are observed for Si samples subjected to heating from ambient to the ceiling temperature of the programme (the derivatograms are not shown for the sake of brevity). This is contrary to its group IV congeners (Ge, Sn and Pb) which show some transformations on heating in a static air atmosphere.

# *Thermoanalysis of the Si-Na<sub>2</sub>S<sub>2</sub>O<sub>8</sub> system*

The derivatograms of various  $Si-Na<sub>2</sub>S<sub>2</sub>O<sub>8</sub>$  molar ratios are depicted in Fig. 1, from which no detectable reaction could be seen between Si and  $Na<sub>2</sub>, S<sub>2</sub>O<sub>8</sub>$ . Nevertheless, the former could catalytically lower the  $T<sub>i</sub>$  of the latter from 180 to 165°C (for the ratios 1 : 4 and 1 : 1), and to  $160$ °C (for the ratios  $1:2$  and  $2:1$ ). Table 1 indicates that the practical and calculated values of the liberated oxygen are almost the same. The melting temperature of Na<sub>2</sub>S<sub>2</sub>O<sub>7</sub> is also lowered (from 385 to 375 $\degree$ C), i.e. by 10 $\degree$ C for the ratios 1:4 and 1:2, and from 385 to 365 $^{\circ}$ C, i.e. by 20 $^{\circ}$ C for the 1:1 and 2:1. Careful examination of the TG curve of the 1 : 4 mixture reveals a small plateau between 215 and 260°C which may be due to an unstable intermediate adduct of Si pyrosulfate, which is so far unknown. Other ratios do not show this plateau. After melting, the pyrosulfate follows the usual route of a two-step decomposition.

The exotherms appearing around  $885^{\circ}$ C for all ratios proved to pertain to redox solid-state reaction between Si and the by-product  $Na<sub>2</sub>SO<sub>4</sub>$ ; the areas under these exotherms increase as the proportion of Si increases. The disappearance of the melting endotherms of  $Na<sub>2</sub>SO<sub>4</sub>$  for the ratios 1:1 and 2 : 1 is due to thermal neutrality, brought about by exo and endotransformations occurring in the same region. XRD patterns for samples heated to 890°C confirm the presence of the mixed oxides  $Na<sub>2</sub>Si<sub>3</sub>O<sub>2</sub>$  (Table 2) in addition to those of unreacted  $Na<sub>2</sub>SO<sub>4</sub>$  and Si [4]. Identical bright d-lines were obtained for the final products at 1050°C which ratify that  $Na_2S_2O_7$  is



Fig. 1. TG and DTA curves for various molar ratios of the  $Si-Na_2S_2O_8$  binary system.

#### TABLE 1





## TABLE 2

d-Spacings<sup>a</sup> versus intensities of bright lines of the 1:1 mixture of Si: Na<sub>2</sub>S<sub>2</sub>O<sub>8</sub> heated to 1000°C

$d(A)$ 4.72		3.46	$3.41$ $2.76$		2.54	2.2	
$I/I_{\alpha}$	$\sim$ 70	100	100 <sub>1</sub>	35	38		

<sup>a</sup> Typical for  $Na<sub>2</sub>Si<sub>3</sub>O<sub>7</sub>$  [5].

thermally stable to beyond the ceiling temperature of the programme. It could be concluded from the above that Si actually reacts with molten  $Na<sub>2</sub>SO<sub>4</sub>$ , therefore several runs for various Si : Na <sub>2</sub>SO<sub>4</sub> ratios were similarly conducted. The 3:1 mixture of  $Si : Na<sub>2</sub>SO<sub>4</sub>$  was found to be the stoichiometric ratio for which the stoichiometric reaction is given as:

$$
Na_2SO_4 + 3 Si + 3 O_2 \xrightarrow{\Delta} Na_2Si_3O_7 + SO_3
$$

A mechanism for this reaction may be proposed. In the presence of excess Si powder, molten  $Na<sub>2</sub>SO<sub>4</sub>$  is catalytically disproportionated to form  $Na<sub>2</sub>O<sub>2</sub>$ and  $SO_2$  ( $SO_2$  gas has been detected experimentally) and in the presence of air or oxygen, a compositional oxidation of Si occurs with  $Na<sub>2</sub>O<sub>2</sub>$  to yield Na,  $Si_3O_7$  (Na<sub>2</sub>SiO<sub>3</sub> · 2SiO<sub>2</sub>); meanwhile SO<sub>2</sub> is instantaneously oxidised by a secondary process to  $SO_3$  with the liberation of excess heat which is indicated by the sharp overlapping exotherms around  $870^{\circ}$ C (in the case of the  $1:1$  ratio) on the DTA derivatogram of Fig. 1. The small weight increase between 840 and 870 $\degree$ C is presumably due to the oxidation of SO<sub>2</sub>, to SO<sub>3</sub>.

## *Thermoanalysis of the*  $Si - K$ *,*  $S$ *,*  $O<sub>s</sub>$  *system*

From the derivatograms of the various molar ratios prepared (Table 3) and subjected to the heating programme (Fig. 2) it seems that, although no reaction occurs between  $K_2S_2O_8$ , or its by-product  $K_2S_2O_7$ , and Si, Si can catalytically lower their  $T_i$  values by 10 and 20 $\degree$ C, respectively. For instance the  $\alpha$  to  $\beta$  phase transition (see DTA curve for the 1:4 ratio) of K,S,O<sub>7</sub> is catalytically shifted from 330 to 310°C; this causes the melting and decomposition endotherms of  $K_2S_2O_7$  to overlap forming a wide, combined endotherm that extends between 330 and 480°C. Beyond 870°C the usual two-step endotherm of the  $K$ ,  $SO_4$  [6] phase change disappears and instead a wide exothermic hump  $(1:4 \text{ ratio})$  appears. As the ratio becomes  $1:2$  it splits into two exo-peaks representing two consecutive reactions, the first due to the formation of  $K_2Si_2O_5$  and  $SO_2$  and the oxidation of the latter,

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Preparation of standard molar ratios and TG results of the  $Si-K_2S_2O_8$  binary mixture





Fig. 2. TG and DTA curves for various molar ratios of the  $Si-K_2S_2O_8$  binary system.

and the second, at 940°C, due to the phase crystallisation of the former which is accompanied by its oxidation. With more Si (ratio  $2:1$ ) the reaction with  $K<sub>2</sub>SO<sub>4</sub>$  becomes more vigorous and the exo-peak, representing the oxidation of SO,, sharpens and becomes steeper near 875°C. Between 870 and 985°C a small weight-gain, probably due to oxidation or polymerisation of  $K_2Si_2O_5$ , is observed; this is indicated by the small exotherm appearing at 940°C. The next smaller exotherm at 985°C may belong to a crystallisation process. Very intense and bright  $d$ -lines (Table 4) as well as calculations from TG curves (Fig. 2) reveal that 91.2 wt.% of  $K_2S_2O_8$  indirectly reacts with Si (Table 3), this convinces us that 2 : 1 is the stoichiometric molar ratio and therefore the stoichiometric reaction is:

$$
K_2S_2O_8 \stackrel{\Delta}{\rightarrow} K_2SO_4 + SO_3 + \frac{1}{2}O_2
$$
  

$$
K_2SO_4 + 2 Si + \frac{3}{2}O_2 \stackrel{\Delta}{\rightarrow} K_2Si_2O_5 + SO_2
$$

### TABLE 4

d-Spacings <sup>a</sup> versus intensities of bright lines for the 2:1 mixture of  $Si-K_2S_2O_8$  heated to  $1000^\circ C$ 

$\bullet$ d(A)	3.80	3.13	3.10	2.96	2.87	2.78	2.43	
$I/I_0$	- 90	50	30	100	60	40	60	

<sup>a</sup> Typical for  $K_2Si_2O_5$  [7].

### **CONCLUSION**

Under a static air atmosphere Si powder was found to be thermally stable up to the end of the heating programme (1050°C). It acts as a semiconductive catalyst to lower the  $T<sub>i</sub>$  values for the thermal decomposition of persulfates or phase transformations of pyrosulfates. At higher temperatures it reacts with solid  $Na<sub>2</sub>SO<sub>4</sub>$  or  $K<sub>2</sub>SO<sub>4</sub>$  to form the mixed oxides  $Na<sub>2</sub>Si<sub>3</sub>O<sub>7</sub>$ and  $K_2Si_2O_5$ , respectively, whose identities were checked by X-ray diffraction. The stoichiometric equations for these solid-state reactions have been established.

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